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Applicant: HASEGAWA et al.

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Group Art Unit: 2813

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Date: December 19, 2001

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U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR					
	BR					
	CR					
	DR					
	ER					
	FR					
	GR					
	HR					
	IR					
	JR					
	KR					
	LR					
	MR					
	NR					

FOREIGN PATENT DOCUMENTS

	Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
					Enclosed	No	Enclose	No
	OR 5-99845	04/1993	Japan	TAKEUCHI et al.	X			X
	PR 11-57390	03/1999	Japan	SHIRAI et al.	X			X
	QR 99/30809	06/1999	WIPO	OHMI	X			X
	RR 11-183366	07/1999	Japan	SATO et al.	X			X
	SR 968 753	01/2000	Europe	OHMI et al.				
	TR							
	UR							
	VR							

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

WR	Masusaki et al., Nippon Sanso Giho (Nippon Sanso Technical Reports), "Monitoring of Impurities in Si Epitaxial Gases by Use of Near-Infrared Laser Diode Spectroscopy," December 3, 1999, No. 18, pp. 32-33			
XR	Microsystem Technology Laboratories Annual Report, Massachusetts Institute of Technology, May 1999			
YR				
ZR				
AAR				
BBR				

Examiner

Date Considered:

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.